
Fabrication of atomically flat silicon carbide surface using catalyst-referred etching (CARE)

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Abstract

A silicon carbide (SiC) has been attracting attention as a material for graphene formation as well as next generation high performance power devices. For these purposes, an atomically flat surface is highly required. In this presentation, we introduce a novel polishing technique called catalyst-referred etching (CARE) which is a chemical polishing method using catalytic reaction and the result of realizing an atomically flat surface of the SiC substrate using CARE process.

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